HOMI BHABHA NATIONAL INSTITUTE

(A University established under Section-3 of the UGC Act, 1956 vide Notification No. F.9-5/2004-U.3 dated June 3, 2005 of Govt. of India)

DGFS-Ph.D. Progrmme (2013) for Engineering Post-Graduates

LOOKING FOR AN OPPORTUNITY TO PURSUE Ph.D.
IN FRONTLINE AREAS IN ENGINEERING SCIENCES
IN STATE-OF-THE-ART LABORATORIES
THEN HOMI BHABHA NATIONAL INSTITUTE IS THE PLACE FOR YOU!

HOMI BHABHA NATIONAL INSTITUTE (HBNI)

invites applications from Engineering Post-Graduates (M. E. / M. Tech./Equivalent Degree) for its DGFS-Ph.D. programme commencing in August 2013

HBNI is a Deemed University comprising of ten institutions of the Department of Atomic Energy (DAE) as its Constituent Institutions (CIs).

For this scheme, the students will be admitted to: (1) Bhabha Atomic Research Centre (BARC), Mumbai; (2) Indira Gandhi Centre for Atomic Research (IGCAR), Kalpakkam; (3) Variable Energy Cyclotron Centre (VECC), Kolkata; (4) Institute for Plasma Research (IPR), Gandhinagar.

These Centers have been in the forefront of research in various branches of engineering viz. mechanical, chemical, metallurgical, electrical, electronics, instrumentation, nuclear and computers. Several of its state-of-the-art laboratories and research facilities are unique to these institutions. The Ph.D. programme in Engineering Sciences is extremely challenging in view of the expanding Nuclear Power Programme of the Department of Atomic Energy. For the motivated candidates, it offers considerable scope to realize their potential while simultaneously contributing to the important task of nation building in this highly specialized area.

Applications are hereby invited from Engineering post-graduates for the award of fellowships under the DAE Graduate Fellowship Scheme for Ph.D. (DGFS-Ph.D.) for pursuing research in an Engineering discipline leading to the award of Ph.D. degree of HBNI. The terms and conditions of the Fellowships are:

- 1. The DGFS-PhD Fellowship is tenable for three years for doing Ph.D. in an Engineering discipline in one of the four R&D centres listed above.
- 2. The amount of Fellowship payable under the scheme is Rs.24000/- per month besides house rent allowance and medical benefits as applicable to DAE.
- 3. The selected Fellows will carry out research under the joint supervision of two guides, one having strength in basic research and the other in technology development.
- 4. After the award of the Ph.D., the DGFS-Ph.D. fellows will have the option to appear for selection under K.S.Krishnan Research Associateship (KSKRA) programme without going through further process of screening. KSKRAs are selected every year and paid a stipend of **Rs.26,000/-** + benefits for a maximum period of 2 years. Anytime during the 2nd year of associateship, subject to satisfactory performance, the KSKRAs will be absorbed in one of the R&D centres of DAE as above and appointed in the Grade Scientific Officer (D) (Approx. emoluments Rs. 58,000) or Scinetific Officer (E) (Approx. emoluments Rs. 65,000) per month

ELIGIBILITY

- **a. Qualifying Degree and other academic qualifications:** Candidates should possess M.E. / M.Tech. or equivalent degree in Mechanical/Chemical/Metallurgical/Nuclear/ Electrical/Electronics/Instrumentation or Computer engineering disciplines with minimum 60% Marks in B. E. /B. Tech. Those who obtained M.Tech based on any other qualifying degree should have secured minimum 60% of marks in that degree and minimum of 60% marks in M. E. / M. Tech. or equivalent degree as per the Ordinance of the respective degree awarding University OR equivalent CGPI (converted to % Marks by multiplying with 100/x if the CGPA is on x points scale).
- b. Age limit: The candidates desirous of availing DGFS-Ph.D. Fellowship should have been born on or after **August 1, 1985**. Age limit is relaxable by three years for OBC and by five years for SC/ST applicants. Persons with Disability (PWD) of all categories are eligible for age relaxation of 10 years. The age limit for the candidates working as faculty in Engineering Colleges desirous of doing Ph.D. without the fellowship grant is 40 years.
- c. Nationality: Applicant should be an Indian citizen.

SELECTION PROCESS

Applicants who fulfill the above mentioned eligibility criteria, and whose M.Tech. project is of relevance to DAE, will be called to BARC, Mumbai on 6th July 2013 for a written screening test followed by interview of selected number of candidates. Screening will be based on previous academic record and performance in the screening test. Selection will be based on performance in interview. The candidates should be prepared for a 10 minutes presentation on their research interest. Outstation applicants called for interview will be paid, after their interview, to and fro sleeper class train fare by shortest route, or actual fare, whichever is

HOW TO APPLY

On one copy of the accompanying application form, affix a passport size photo, sign across and, along with attested copies of documents mentioned in the application, and one additional photo, mail to:

 $HBNI-DGFS-Ph.D.\ Programme-August\ 2013\ (Engineering\ Post-graduates)$

Administrative Officer- III, HBNI

 $Training\ School\ Complex, Anushaktina gar$

Mumbai - 400 094.

Applicants are advised to mail only by registered or speed post services and to preserve the receipt for future reference.

Last Date for receipt of Applications: May 10, 2013 For further details visit our website www.hbni.ac.in

HOMI BHABHA NATIONAL INSTITUTE Application for DGFS-Ph.D.-August 2013 (Engineering Post-Graduates)

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1. Name:						
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6. Category: General	□ SC□ ST□ OF	вс 🗆	7. Whether pe	rson with disability (P	WD): Yes 🗌 No 🕻	
8. Nationality:						
9. Qualifying degree:	M. E, M. Tech	Equivalent 🗌				
9a.If equivalent, give	details:					
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-		_	Metallurgical Engg.	_	_	uclear Engg.
11. Specialization:			12. Univer	sity:		
13. Whether result of	qualifying degree available:	Yes/No.				
14. Academic Records	:	T	T			
Qualification	BE/B.Tech/B.Sc(Engg)	GATE	ME/M.Tech/Equivalent (up to the last semester/ term for which result is available)			
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Score secured						
Total score						
Total score % of total						
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Last Date for receipt of Applications: May 10, 2013 Forms can also be downloaded from www.hbni.ac.in